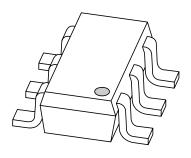
DISCRETE SEMICONDUCTORS

DATA SHEET



BC817DPNNPN/PNP general purpose transistor

Product data sheet Supersedes data of 2002 Aug 09 2002 Nov 22



NPN/PNP general purpose transistor

BC817DPN

FEATURES

- High current (500 mA)
- 600 mW total power dissipation
- Replaces two SOT23 packaged transistors on same PCB area.

APPLICATIONS

- General purpose switching and amplification
- · Complementary driver
- Half and full bridge driver.

DESCRIPTION

NPN/PNP transistor pair in a SOT457 (SC-74) plastic package.

MARKING

TYPE NUMBER	MARKING CODE		
BC817DPN	N4		

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT	
V_{CEO}	collector-emitter voltage	45	V	
I _C	collector current (DC)	500	mA	
I _{CM}	peak collector current	1	Α	

PINNING

PIN	DESCRIPTION	
1, 4	emitter	TR1; TR2
2, 5	base	TR1; TR2
6, 3	collector	TR1; TR2

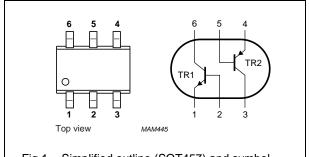


Fig.1 Simplified outline (SOT457) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per transis	Per transistor; for the PNP transistor with negative polarity					
V_{CBO}	collector-base voltage	open emitter	-	50	V	
V_{CEO}	collector-emitter voltage	open base	-	45	V	
V _{EBO}	emitter-base voltage	open collector	-	5	V	
I _C	collector current (DC)		-	500	mA	
I _{CM}	peak collector current		-	1	Α	
I _{BM} peak base current			-	200	mA	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	370	mW	
T _{stg}	storage temperature		-65	+150	°C	
Tj	junction temperature		-	150	°C	
T _{amb}	operating ambient temperature		-65	+150	°C	
Per device	•					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	600	mW	

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	208	K/W

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

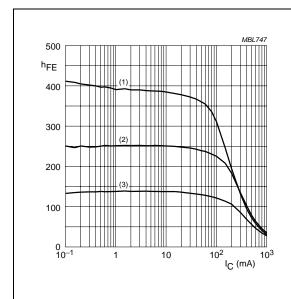
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	Per transistor unless otherwise specified; for the PNP transistor with negative polarity					
I _{CBO}	collector-base cut-off current	V _{CB} = 20 V; I _E = 0	_	_	100	nA
		V _{CB} = 20 V; I _E = 0; T _j = 150 °C	_	-	5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	_	_	100	nA
h _{FE}	DC current gain	V _{CE} = 1 V; I _C = 100 mA; note 1	160	-	400	
		V _{CE} = 1 V; I _C = 500 mA; note 1	40	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 500 \text{ mA}$; $I_B = 50 \text{ mA}$; note 1	_	-	700	mV
V _{BE}	base-emitter voltage	V _{CE} = 1 V; I _C = 500 mA; notes 1 and 2	-	-	1.2	V
NPN trans	NPN transistor					
Сс	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	5	_	pF
f _T	transition frequency	V _{CE} = 5 V; I _C = 10 mA; f = 100 MHz	100	-	_	MHz
PNP trans	istor					
Сс	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	9	-	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA};$ f = 100 MHz	80	_	_	MHz

Notes

- 1. Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$
- 2. V_{BE} decreases by approximately -2 mV/K with increasing temperature.

NPN/PNP general purpose transistor

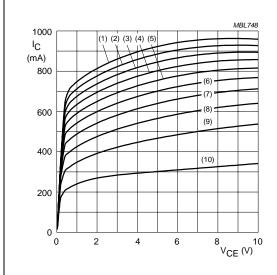
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TR1 (NPN) $V_{CE} = 1 V$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.2 DC current gain as a function of collector current; typical values.



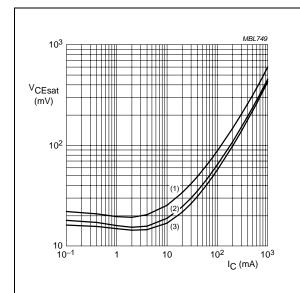
TR1 (NPN)

- (1) $I_B = 15 \text{ mA}.$
 - (5) $I_B = 9 \text{ mA}$. (6) $I_B = 7.5 \text{ mA}$.
- (9) $I_B = 3 \text{ mA}$. (10) $I_B = 1.5 \text{ mA}$.
- (2) $I_B = 13.5 \text{ mA}$. (3) $I_B = 12 \text{ mA}$.
- (7) $I_B = 6 \text{ mA}.$
- (4) $I_B = 10.5 \text{ mA}.$
- (8) $I_B = 4.5 \text{ mA}.$

Fig.3 Collector current as a function of collector-emitter voltage; typical values.

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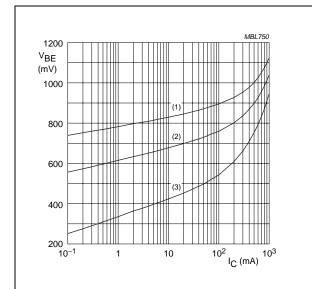
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TR1 (NPN) $I_C/I_B = 10$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



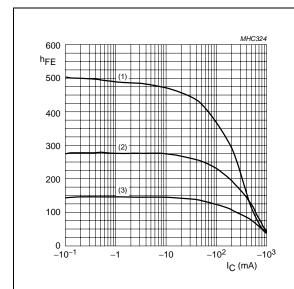
TR1 (NPN) V_{CE} = 1 V.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.5 Base-emitter voltage as a function of collector current; typical values.

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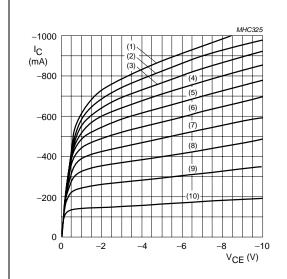
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TR2 (PNP) $V_{CE} = -1 V$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.6 DC current gain as a function of collector current; typical values.



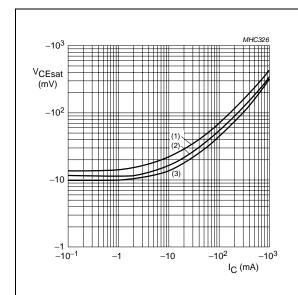
TR2 (PNP)

- (1) $I_B = -7 \text{ mA}$.
- (5) $I_B = -4.2 \text{ mA}.$ (6) $I_B = -3.5 \text{ mA}.$
- (9) $I_B = -1.4 \text{ mA}.$ (10) $I_B = -0.7 \text{ mA}.$
- (2) $I_B = -6.3 \text{ mA}.$ (3) $I_B = -5.6 \text{ mA}.$
- (6) $I_B = -3.5 \text{ mA}$
- (7) $I_B = -2.8 \text{ mA}.$
- (4) $I_B = -4.9 \text{ mA}$. (8) $I_B = -2.1 \text{ mA}$.

Fig.7 Collector current as a function of collector-emitter voltage; typical values.

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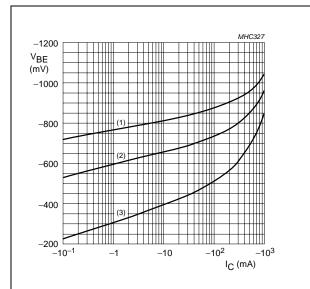
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TR2 (PNP) $I_{\rm C}/I_{\rm B} = 10$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



TR2 (PNP) $V_{CE} = -1 \ V.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.9 Base-emitter voltage as a function of collector current; typical values.

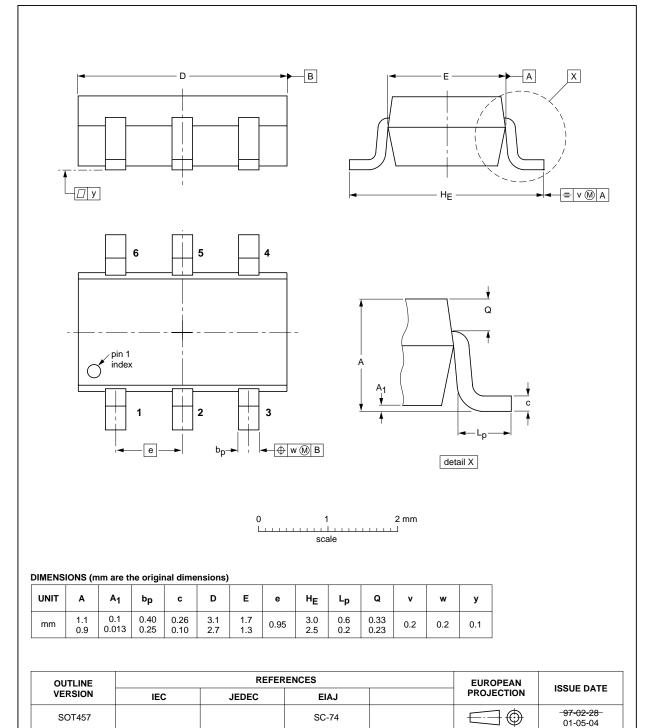
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT457



NPN/PNP general purpose transistor

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
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Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
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